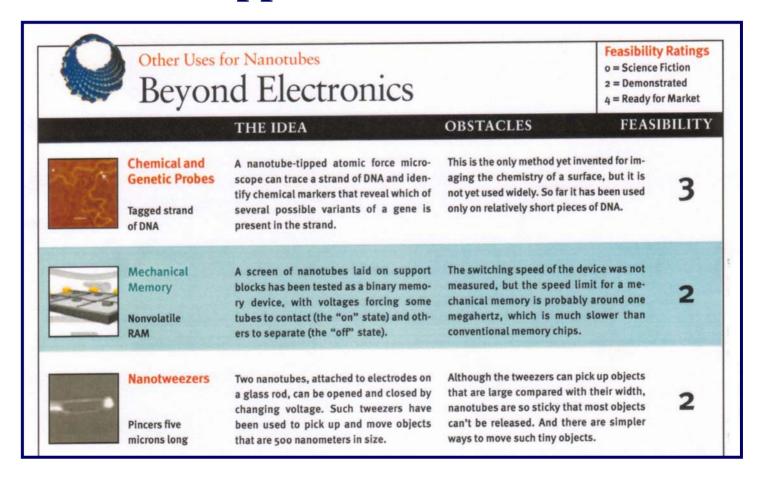
## Nanomaterials

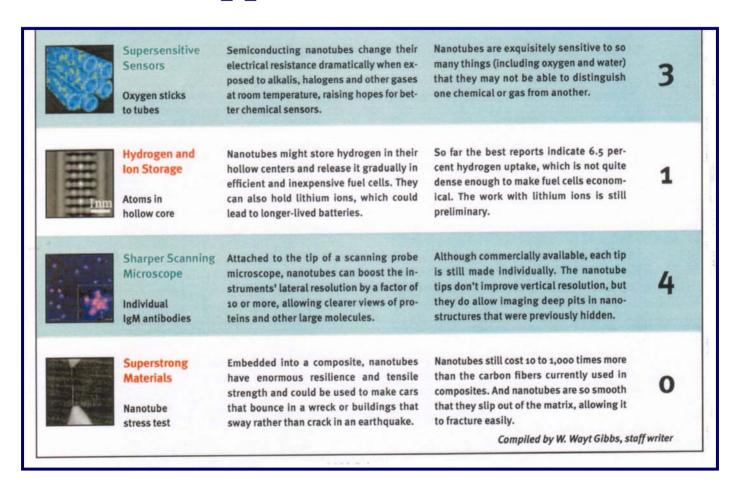
Lecture 7: Carbon Nanomaterials

#### Other Applications of Nanotubes



P. G. Collins and Ph. Avouris, *Scientific American*, **283**, 62 (2000).

### Other Applications of Nanotubes



P. G. Collins and Ph. Avouris, *Scientific American*, **283**, 62 (2000).

#### **Density of States**

In general, the density of states in *d*-dimensions is:

$$D(E) = \left(\frac{L}{2\pi}\right)^{d} \int \frac{\delta(k(E) - k)dk^{d}}{\left|\nabla_{k}(E)\right|}$$

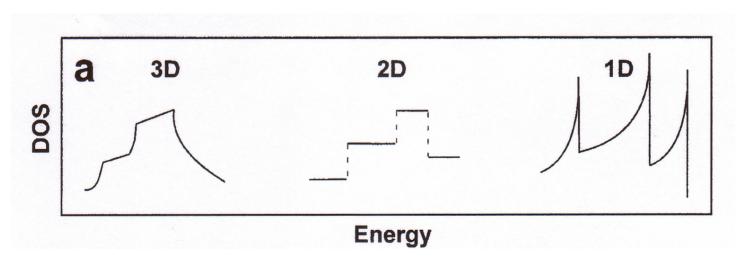
At band edges, 
$$|\nabla_k(E)| = 0$$

→ van Hove singularities in the density of states

T. W. Odom, et al., J. Phys. Chem. B, 104, 2794 (2000).

### **Nanotube 1-D Density of States**

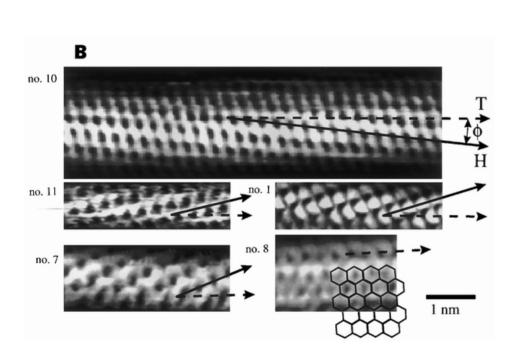
The van Hove singularities assume different forms based on the dimensionality of the system:

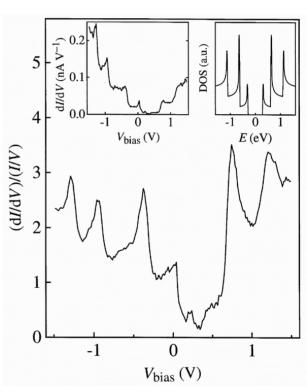


The 1-D nature of nanotubes leads to peaks in the density of states.

T. W. Odom, et al., J. Phys. Chem. B, 104, 2794 (2000).

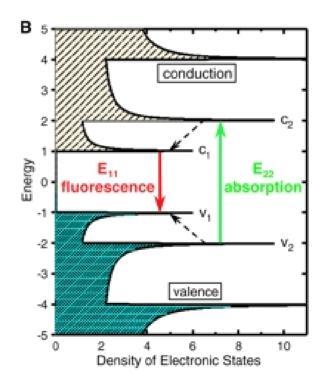
# STM Measurements of Nanotube van Hove Singularities





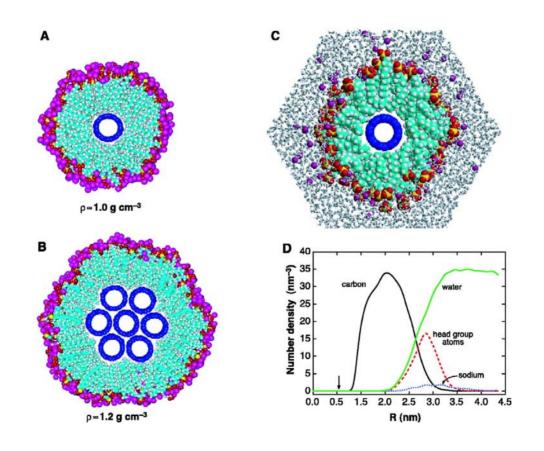
J. W. G. Wilder, et al., Nature, 391, 59 (1998).

## Implications of van Hove Singularities for Nanotube Optical Properties



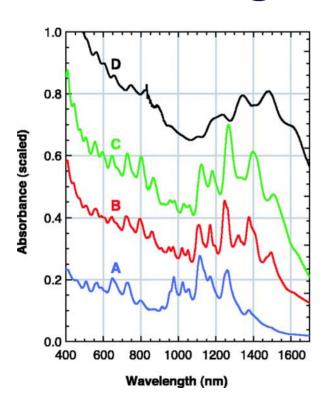
S. M. Bachilo, et al., Science, 298, 2361 (2002).

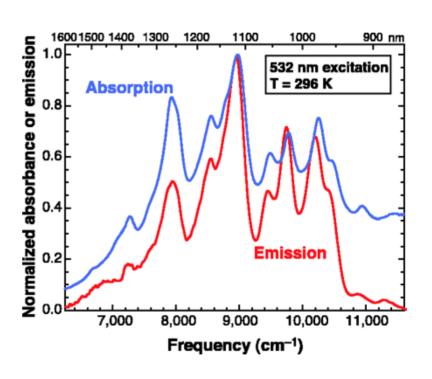
#### **Separating Carbon Nanotubes in Solution**



M. J. O'Connell, et al., Science, 297, 593 (2002).

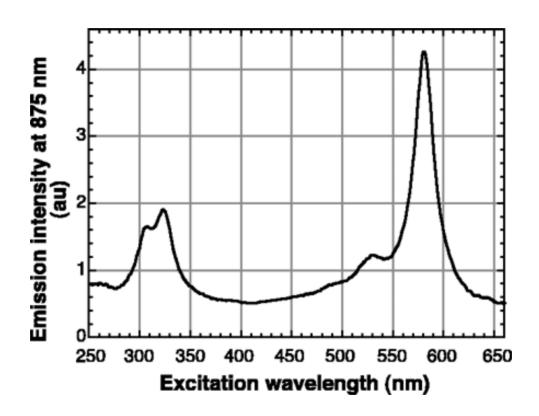
# Band Gap Absorption and Fluorescence from Individual Single-Walled Carbon Nanotubes





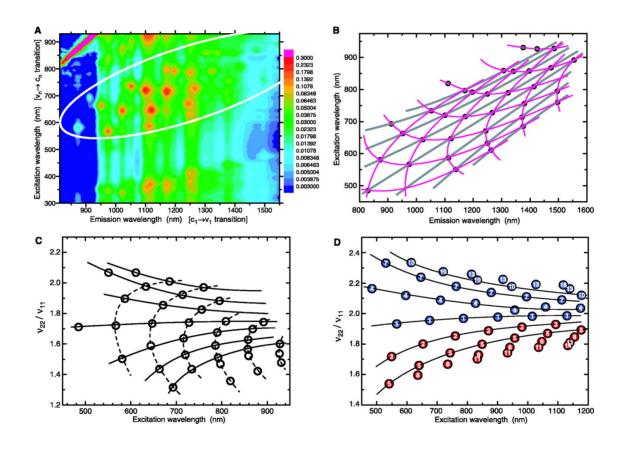
M. J. O'Connell, et al., Science, 297, 593 (2002).

### Excitation at the $E_{22}$ Transition



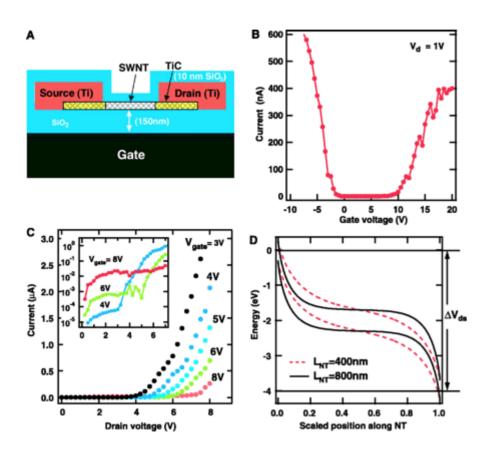
M. J. O'Connell, et al., Science, 297, 593 (2002).

#### Structure-Assigned Optical Spectra



S. M. Bachilo, et al., Science, 298, 2361 (2002).

#### **Ambipolar Carbon Nanotube FET**



**Fig. 1.** (**A**) Schematic diagram of the ambipolar s-SWNT device structure. (**B**) Electrical characterization of a typical ambipolar device. A plot of the drain current versus Vg for a grounded source and a small drain potential of 1Vis shown. The data indicate ambipolar behavior. (**C**) Plot of the drain current versus Vg for a grounded source and a gate potential of 5V for the device used in the optical measurements. The inset shows the data on a logarithmic scale. (**D**) Calculated band structure for carbon nanotube FET devices with Vg = 4V and Vg halfway between the source and drain voltages.

J. A. Misewich, et al., Science, 300, 783 (2003).

#### Infrared Emission from an Ambipolar Nanotube FET

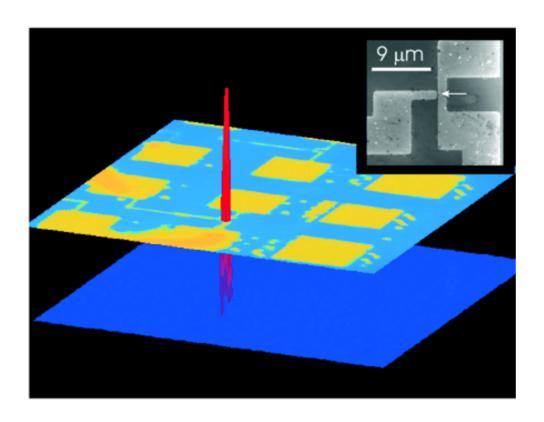
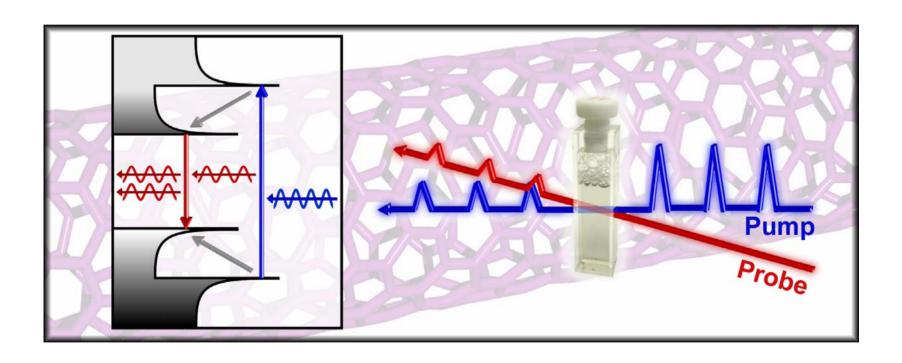


Fig. 2. Optical emission from an ambipolar carbon nanotube FET detected with an IR camera. The upper plane is a color-coded IR image of the carbon nanotube FET. The contact pads and thin wires leading to the carbon nanotube channel are shown in yellow. The lower plane is the surface plot of the IR emission image taken under conditions of simultaneous e— and h+ injection into the carbon nanotube. The emission was localized at the position of the carbon nanotube. (Inset) SEM showing the device structure in the region of the nanotube emitter.

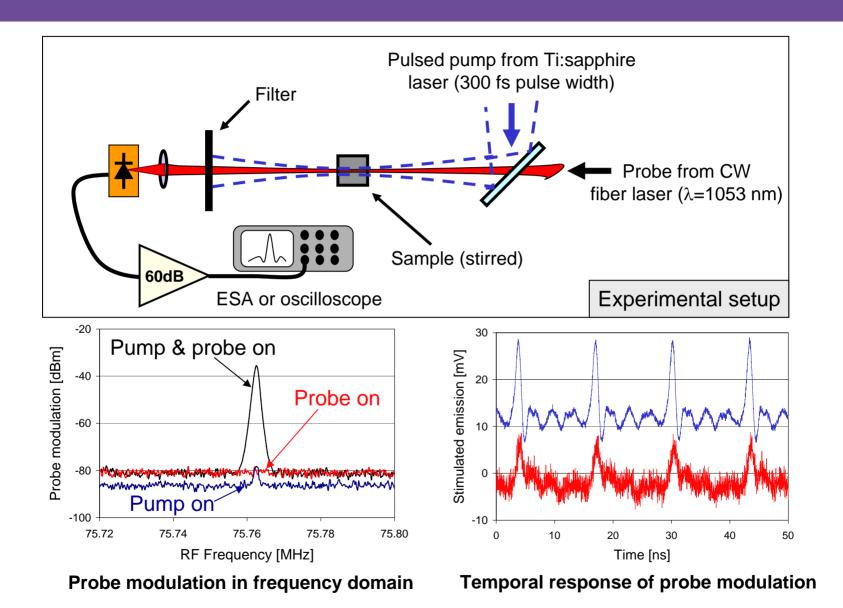
J. A. Misewich, et al., Science, 300, 783 (2003).

## Characterization of Stimulated Emission from Encapsulated SWNTs

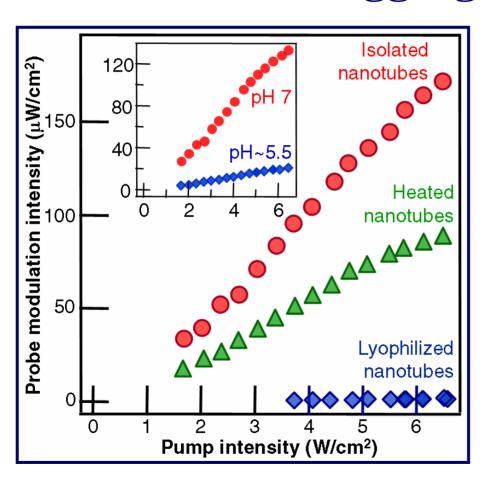


M. S. Arnold, et al., Nano Letters, 3, 1549 (2003).

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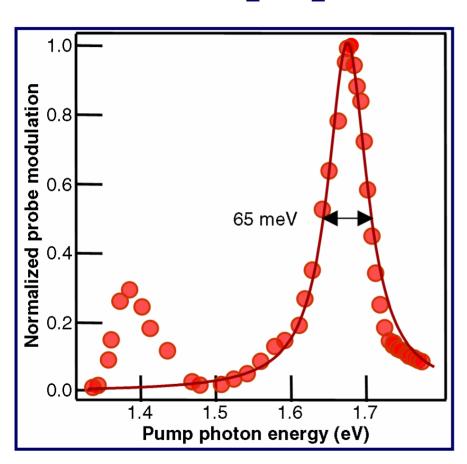
## Effect of Aggregation and pH



- Aggregation of isolated nanotubes by lyophilization and re-suspension drastically reduces probe modulation intensity by a factor of 122.
- Photobleaching disappears at acidic pH and is reversibly restored at neutral and basic pH, consistent with protonation of nanotube sidewalls at acidic pH.

M. S. Arnold, et al., Nano Letters, 3, 1549 (2003).

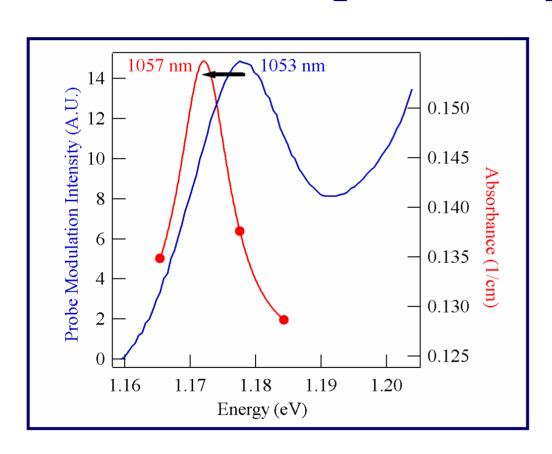
## **Pump Spectral Dependence**



- The measured  $E_{22}$  transition width of 65 meV is consistent with fast electron-electron scattering on the 300 fs time scale.
- The feature near 1.4 eV is likely due to a Raman effect (the measured difference between pump and probe energies is ~ 1600 cm<sup>-1</sup>, which matches the G-band Raman mode in SWNTs).

M. S. Arnold, et al., Nano Letters, 3, 1549 (2003).

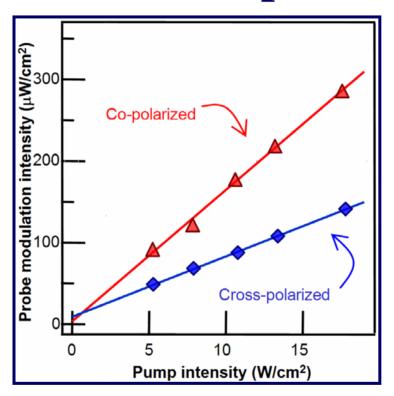
### **Probe Spectral Dependence**



- The probe modulation spectrum is slightly red-shifted from the absorbance spectrum by 45 cm<sup>-1</sup>.
- From a Lorentzian fit, the width of the  $E_{11}$  transition is only 10 meV compared with 65 meV as measured for the  $E_{22}$  transition.

M. S. Arnold, et al., Nano Letters, 3, 1549 (2003).

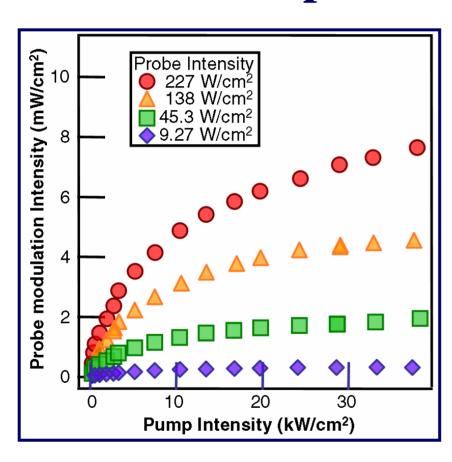
## **Polarization Dependence**



Co-polarized pump and probe lead to greater photobleaching than cross-polarized as expected for a 1-D system.

M. S. Arnold, et al., Nano Letters, 3, 1549 (2003).

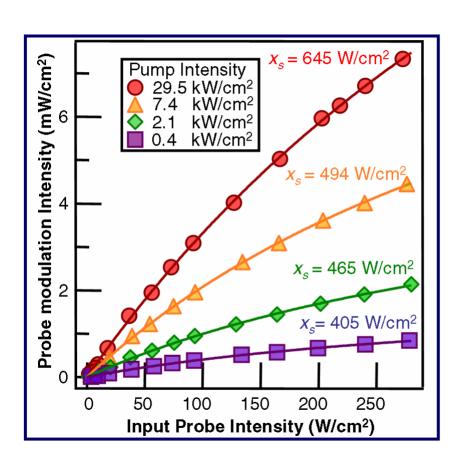
## **Pump Saturation Effects**



- At low pump intensities below 10 W/cm<sup>2</sup>, linear behavior is observed.
- Saturation of the probe modulation is consistent with:
  - ➤ Increased multi-particle Auger recombination for large carrier densities.
  - Exciton-exciton annihilation effects.
  - > Saturation and filling of a finite number of states.

M. S. Arnold, et al., Nano Letters, 3, 1549 (2003).

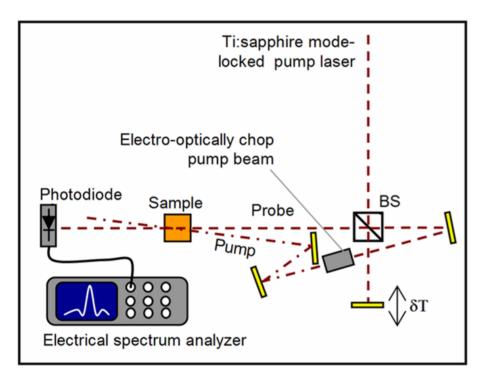
#### **Probe Saturation Effects**



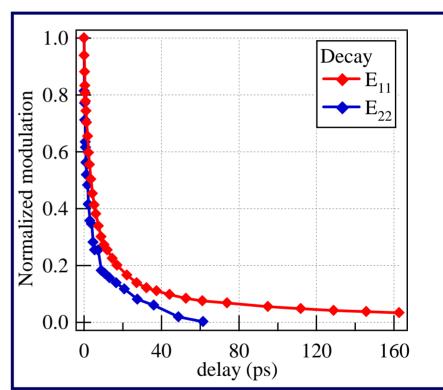
- $x_S$  corresponds to the probe intensity for which the rate of stimulated recombination is equal to the intrinsic rate of recombination.
- An increase in  $x_s$  at large pump intensities is consistent with an increase in the effective interband recombination rate due to enhanced Auger recombination for large carrier densities.

M. S. Arnold, et al., Nano Letters, 3, 1549 (2003).

## **Degenerate Pump-Probe Measurements**



Degenerate pump-probe optical setup.



Time-resolved relaxation at  $E_{11}$  (975 nm) and  $E_{22}$  (740 nm) optical transitions.